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<u>Diodes Incorporated</u> <u>ZXMP3A16GTA</u>

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Datasheet of ZXMP3A16GTA - MOSFET P-CH 30V 4.6A SOT223

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A Product Line of Diodes Incorporated



ZXMP3A16G

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	I _D max T _A = +25°C (Note 6)
-30V	$45m\Omega$ @ $V_{GS} = -10V$	-7.5A
-307	$70m\Omega$ @ $V_{GS} = -4.5V$	-5.9A

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Relay and Solenoid Driving

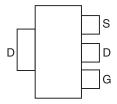
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.112 grams (Approximate)

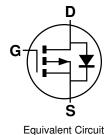
SOT223



Top View



Pin Out - Top View



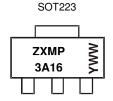
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP3A16GTA	ZXMP3A16	7	12	1,000
ZXMP3A16GTC	ZXMP3A16	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds. All applicable RoHS exemptions applied. Further information about Diodes Inc.'s "Green" Policy can be found on our website.

Marking Information



ZXMP3A16 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or \overline{W} W = Week Code (01~53)



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ZXMP3A16G

Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V _{GS}	±20	V
		(Note 6)		-7.5	
Continuous Drain Current	$V_{GS} = 10V$	T _A = +70 °C (Note 6)	I_{D}	-6.0	Α
		(Note 5)		-5.4	
Pulsed Drain Current	$V_{GS} = 10V$	(Note 7)	I _{DM}	-24.9	A
Continuous Source Current (Body diode) (Note 6)		Is	-3.2	Α	
Pulsed Source Current (Body diode) (Note 7)		I _{SM}	-24.9	A	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	В	2.0 16		
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5) (Note 6)	R _{θJA}	62.5 32.2	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ heta JL}$	8.51		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C		

Notes:

- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note (5), except the device is measured at $t \le 10$ sec.
- 7. Same as Note (5), except the device is pulsed with D= 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
- 8. Thermal resistance from junction to solder-point (at the end of the drain lead).

Datasheet of ZXMP3A16GTA - MOSFET P-CH 30V 4.6A SOT223

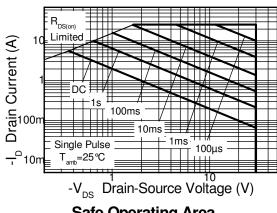
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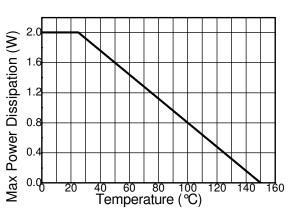


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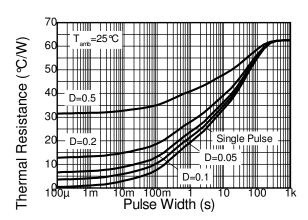
Thermal Characteristics



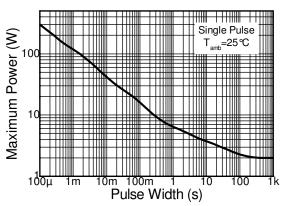
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



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ZXMP3A16G

Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test (Condition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_		V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -30V, V_{G}$	s = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{I}$	os = 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0	_		V	$I_D = -250 \mu A, V_D$	os = V _G S
Static Drain-Source On-Resistance (Note 9)	D			45	mΩ	$V_{GS} = -10V, I_D$	= -4.2A
Static Drain-Source On-Nesistance (Note 9)	R _{DS} (ON)	_	_	70	mΩ	$V_{GS} = -4.5V, I_{D}$	= -3.4A
Forward Transconductance (Notes 9 & 10)	9 _{fs}	_	9.2	_	S	$V_{DS} = -15V, I_{D}$	= -4.2A
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.85	-0.95	V	$I_S = -3.6A, V_{GS}$	= 0V, T _J = +25 ℃
Reverse Recovery Time (Note 10)	t _{rr}		21.7	_	ns	$I_F = -2A$, $di/dt = 100A/\mu s$, $T_J = +25$ °C	
Reverse Rsecovery Charge (Note 10)	Q _{rr}	_	16.1		nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1,022	_	pF	\/ 4E\/ \/	01/
Output Capacitance	Coss	_	267	_	pF	$V_{DS} = -15V, V_{G}$ $f = 1MHz$	S = UV
Reverse Transfer Capacitance	C _{rss}	_	229	_	pF	1 = 11VII 12	
Total Gate Charge (Note 11)	Qg	_	17.2	_	nC	$V_{GS} = -5V$	
Total Gate Charge (Note 11)	Qg	_	29.6	_	nC	$V_{DS} = -15V$ $I_{D} = -4.2A$	
Gate-Source Charge (Note 11)	Qgs	_	2.8	_	nC		
Gate-Drain Charge (Note 11)	Q _{gd}	_	8.6	_	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	3.8	_	ns	V_{DD} = -15V, V_{GS} = -10V I_D = -1A, $R_G \cong 6.0\Omega$	
Turn-On Rise Time (Note 11)	t _r		6.5	_	ns		
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	37.1	_	ns		
Turn-Off Fall Time (Note 11)	t _f		21.4	_	ns		

Notes:

- 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$
- 10 . For design aid only, not subject to production testing.
 11 . Switching characteristics are independent of operating junction temperatures.



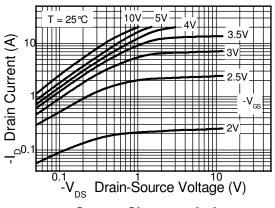
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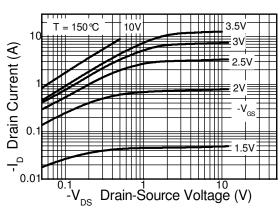


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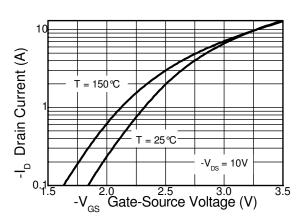
Typical Characteristics



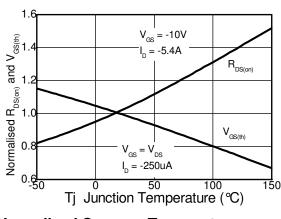
Output Characteristics



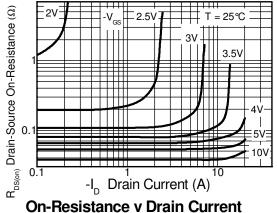
Output Characteristics

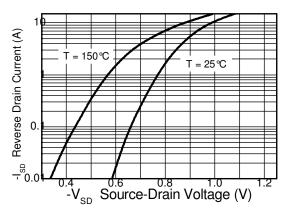


Typical Transfer Characteristics



Normalised Curves v Temperature





Source-Drain Diode Forward Voltage

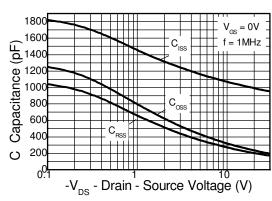
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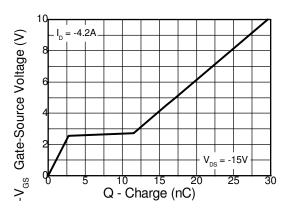
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Typical Characteristics (continued)

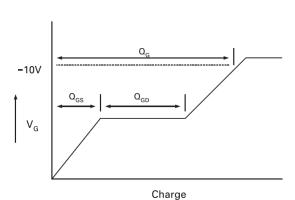


Capacitance v Drain-Source Voltage

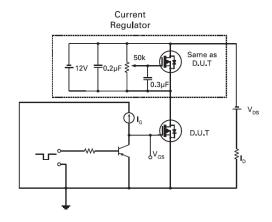


Gate-Source Voltage v Gate Charge

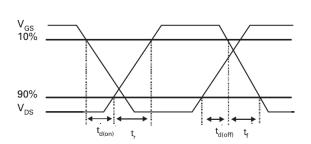
Test Circuits



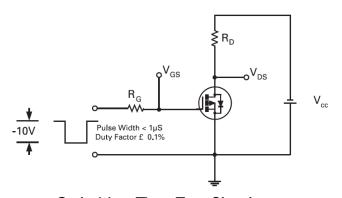
Basic Gate Charge Waveform



Gate Charge Test Circuit



Switching Time Waveforms



Switching Time Test Circuit

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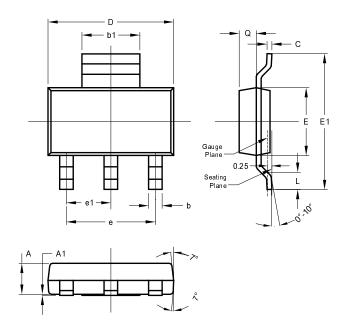




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Package Outline Dimensions

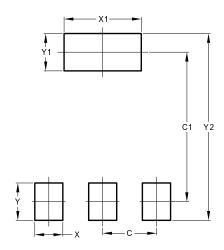
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A 1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



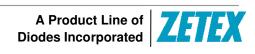
Dimensions	Value (in mm)	
С	2.30	
C1	6.40	
Х	1.20	
X1	3.30	
Υ	1.60	
Y1	1.60	
Y2	8.00	



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